

Esa Scc Screened Surface Temperature Sensor Model 0118mm

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This SpringerBrief discusses the determination and classification of the ambient temperature corrosion and stress corrosion properties of aerospace structural alloys, with emphasis on (1) aluminium alloys, modern (3rd generation) aluminium-lithium alloys, stainless steels and titanium alloys and (2) some of the issues involved. Standard /reference data on environmental properties, including corrosion and stress corrosion, are mandatory for the qualification and certification of materials for aerospace vehicles, and also for the design of actual structures and components. Recommendations for further testing and evaluation are given at appropriate points in the text. The book concludes with a summary of the main topics.

An annual book providing overviews of the world's space programmes and organizations. Coverage includes past, current and future programmes, details of individual companies and their activities, military space programmes such as SDI, and Soviet activities. Available on CD-ROM and EIS.

A selection of annotated references to unclassified reports and journal articles that were introduced into the NASA scientific and technical information system and announced in Scientific and technical aerospace reports (STAR) and International aerospace abstracts (IAA).

Silicon technology today forms the basis of a world-wide, multi-billion dollar component industry. The reason for this expansion can be found not only in the physical properties of silicon but also in the unique properties of the silicon-silicon dioxide interface. However, silicon devices are still subject to undesired electrical phenomena called "instabilities". These are due mostly to the imperfect nature of the insulators used, to the not-so-perfect silicon-insulator interface and to the generation of defects and ionization phenomena caused by radiation. The problem of instabilities is addressed in this volume, the third of this book series. Vol.3 updates and supplements the material presented in the previous two volumes, and devotes five chapters to the problems of radiation-matter and radiation-device interactions. The volume will aid circuit manufacturers and circuit users alike to relate unstable electrical parameters and characteristics to the presence of physical defects and impurities or to the radiation environment which caused them.

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